

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

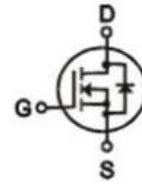
• Features

- Advance device constructure
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- Synchronous Rectification for AC-DC/DC-DC converter
- Power Tools

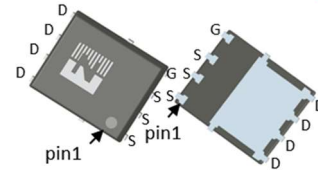
• Product Summary



$$V_{DS} = 120V$$

$$R_{DS(ON)} = 12m\Omega$$

$$I_D = 75A$$



DFN5 x 6

• Ordering Information:

Part NO.	ZMS110N12N
Marking	ZMS110N12
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	75	A
	$I_{D@TC=75^\circ C}$	57	A
	$I_{D@TC=100^\circ C}$	47	A
Pulsed Drain Current ^①	I_{DM}	225	A
Total Power Dissipation($TC=25^\circ C$)	$P_{D@TC=25^\circ C}$	85	W
Total Power Dissipation($TA=25^\circ C$)	$P_{D@TA=25^\circ C}$	3.4	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy@ $L=0.1mH$	E_{AS}	80	mJ
Avalanche Current@ $L=0.1mH$	I_{AS}	40	A

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	37	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	120			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.3	1.7	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 120V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 30A$		12	15	m Ω
		$V_{GS} = 4.5V, I_D = 20A$		14	18	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 40A$		18		s
Diode Forward Voltage	V_{FSD}	$I_S = 30A$			1.2	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$V_{DS} = 25V$ $f = 1MHz$	-	2420	-	pF
Output capacitance	C_{oss}		-	960	-	
Reverse transfer capacitance	C_{rss}		-	54	-	

•Switching Parameters ($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD} = 30V$	-	28	-	nC
Gate - Source charge	Q_{gs}	$I_D = 10A$	-	3.8	-	
Gate - Drain charge	Q_{gd}	$V_{GS} = 10V$	-	5.9	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS} = 10V,$		15		ns
Turn-ON Rise time	t_r	$V_{DS} = 50V, R$		17		
Turn-Off Delay time	$t_{D(off)}$	$= 0.75\Omega, R = 6\Omega$		96		

Turn-Off Fall time	t_f		76		
Body Diode Reverse Recovery Time	t_{rr}	$I_F=20A$, $dI/dt=100A/\mu s$	56		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=20A$, $dI/dt=100A/\mu s$	38		nC

Note: ① Pulse Test : Pulse width $\leq 10\mu s$, Duty cycle $\leq 1\%$;

Fig.1 Gate-Charge Characteristics

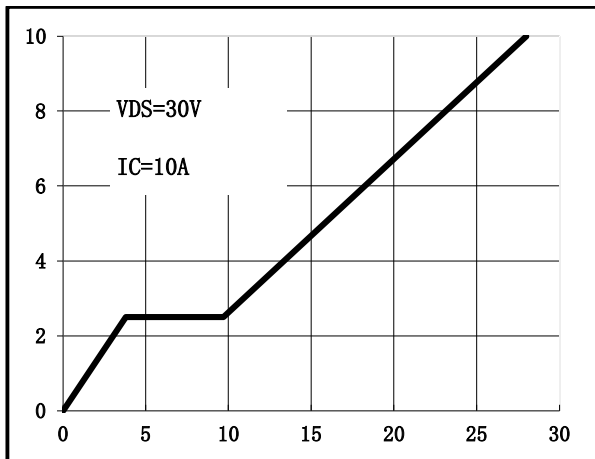


Fig.2 Capacitance Characteristics

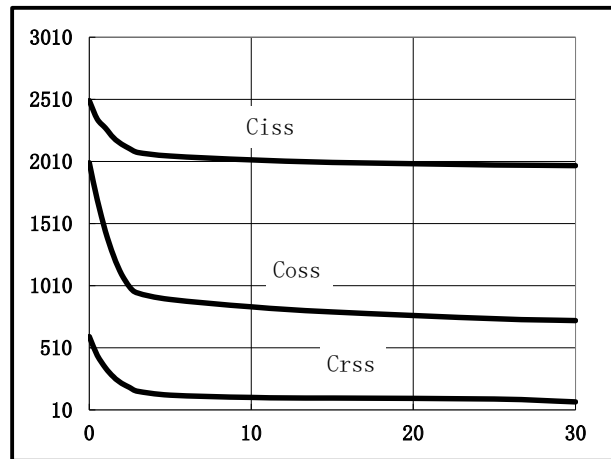


Fig.3 Power Dissipation

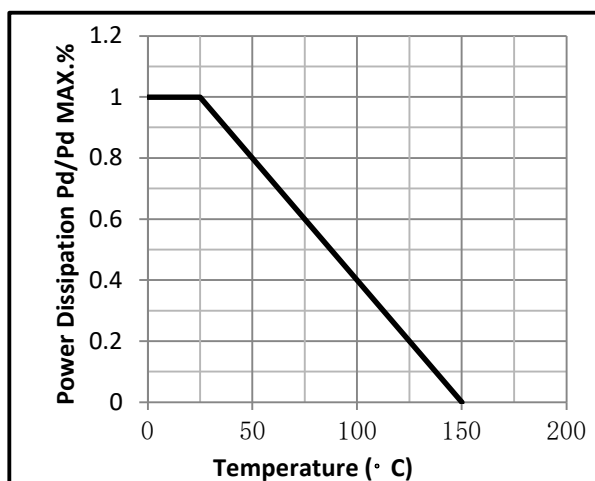


Fig.4 Typical output Characteristics

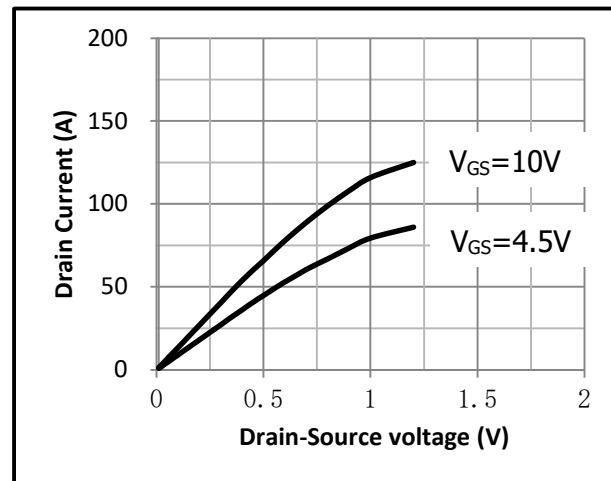


Fig.5 Threshold Voltage V.S Junction Temperature Fig.6 Resistance V.S Drain Current

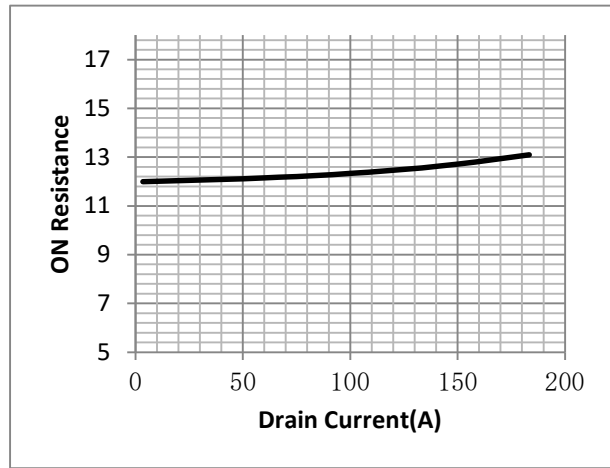
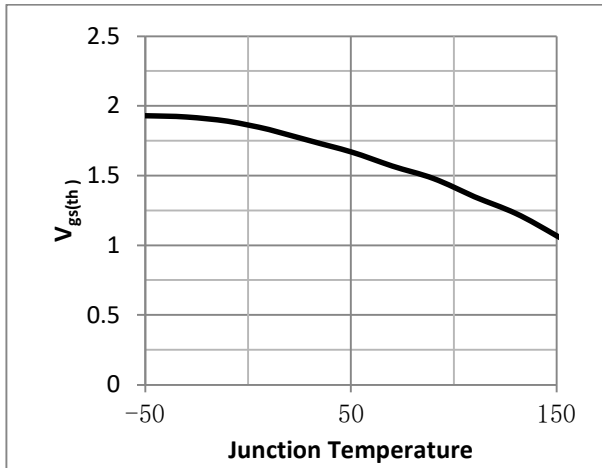


Fig.7 On-Resistance VS Gate Source Voltage

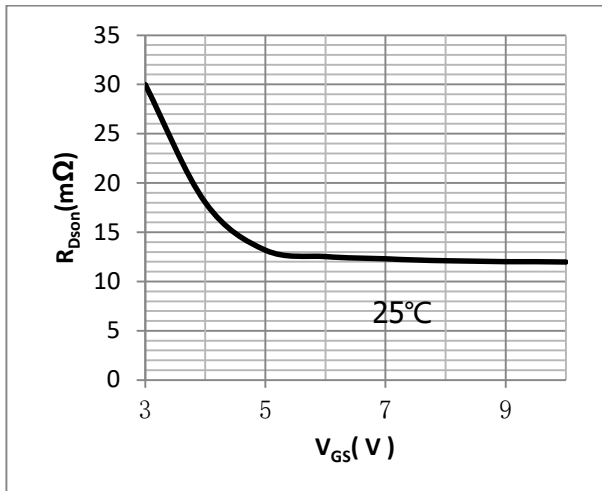


Fig.8 On-Resistance V.S Junction Temperature

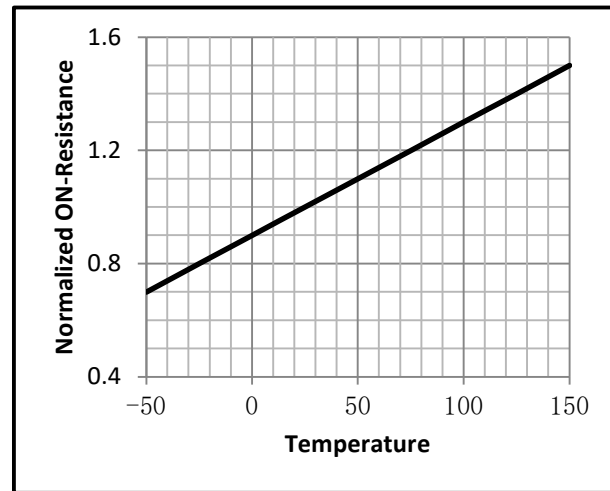


Fig.9 Gate Charge Measurement Circuit

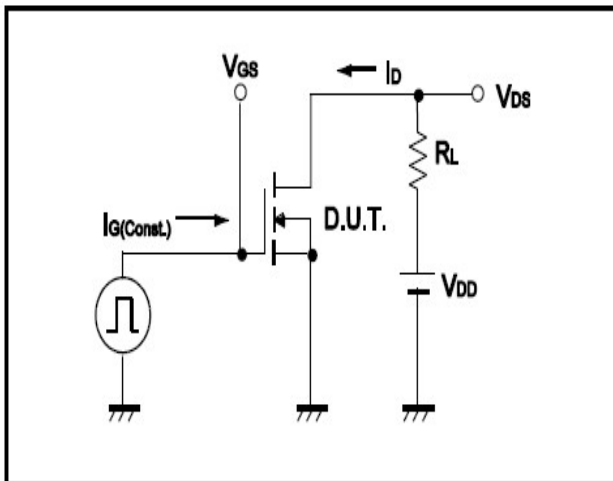


Fig.10 Gate Charge Waveform

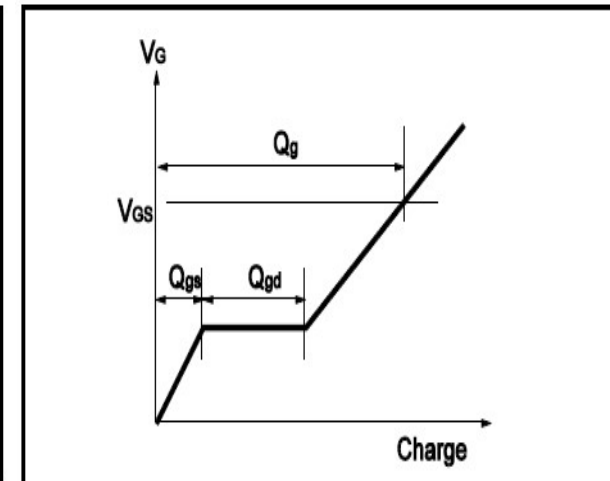


Fig.11 Switching Time Measurement Circuit

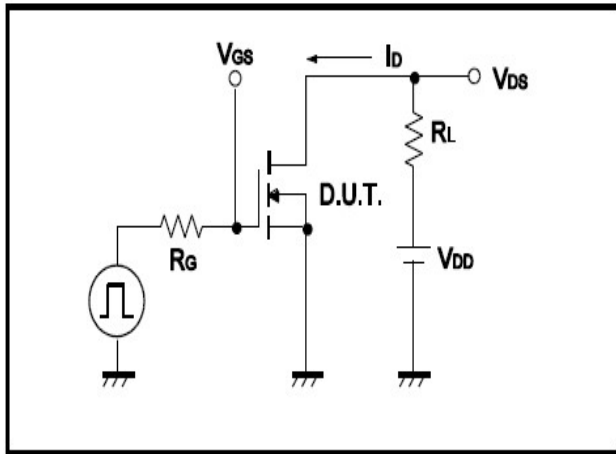
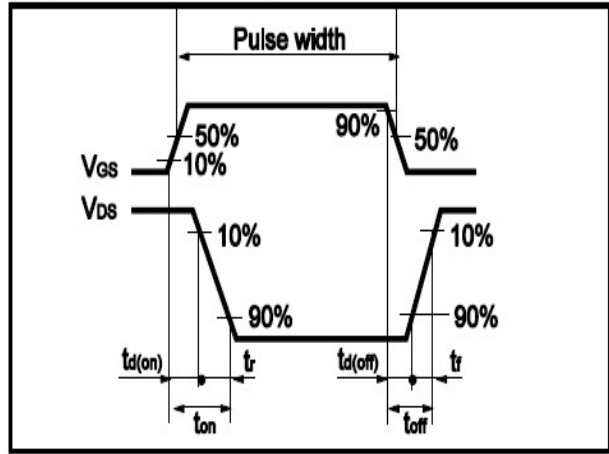


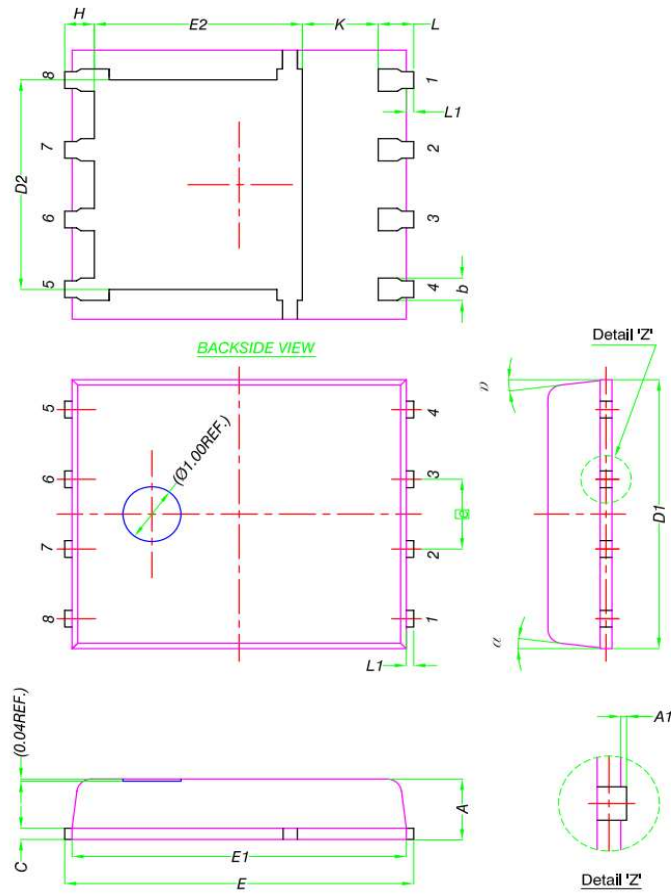
Fig.12 Switching Time Waveform





●Dimensions (DFN5×6)

Unit: mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°